

SANYO	No.1430B	2SC3495
	NPN Epitaxial Planar Silicon Transistor High h_{FE} , Low-Frequency General-Purpose Amp Applications	

Use

- . AF amp, various driver, muting circuit.

Features

- . Adoption of FBET process.
- . High DC current gain ($h_{FE}=500$ to 2000).
- . High breakdown voltage ($V_{CEO} \geq 100V$).
- . Low collector to emitter saturation voltage ($V_{CE(sat)} \leq 0.5V$).
- . High V_{EBO} ($V_{EBO} \geq 15V$).
- . Small c_{ob} ($c_{ob}=1.8pF$ typ)

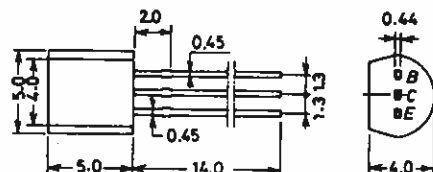
Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Collector to Base Voltage	V_{CB0}	120	V
Collector to Emitter Voltage	V_{CE0}	100	V
Emitter to Base Voltage	V_{EBO}	15	V
Collector Current	I_C	50	mA
Collector Current(Pulse)	I_{CP}	100	mA
Base Current	I_B	10	mA
Collector Dissipation	P_C	500	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=80V, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=10V, I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=10mA$	500	1000	2000	
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=10mA$		170		MHz
Output Capacitance	c_{ob}	$V_{CB}=10V, f=1MHz$		1.8		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=200\mu A$	0.1	0.5		V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_E=200\mu A$	0.7	1.0		V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	120			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	100			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	15			V

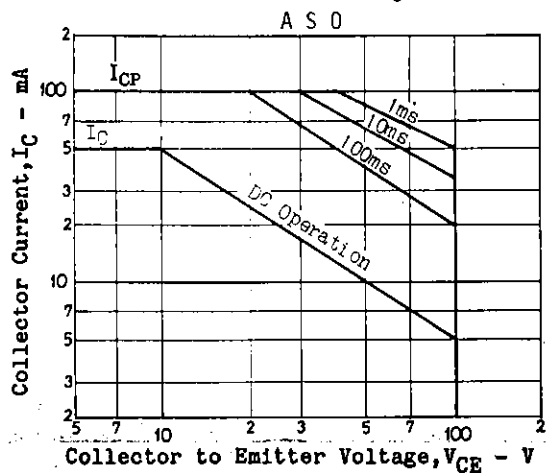
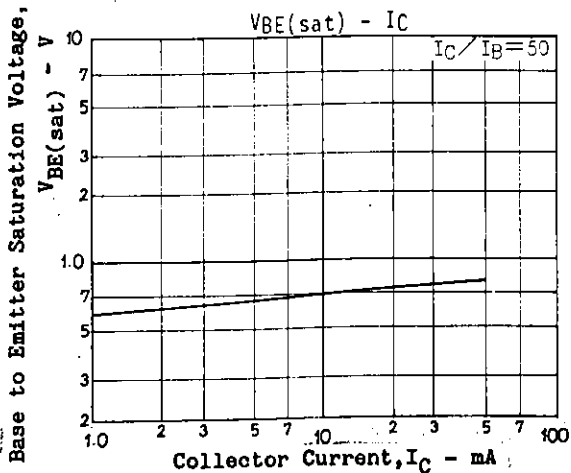
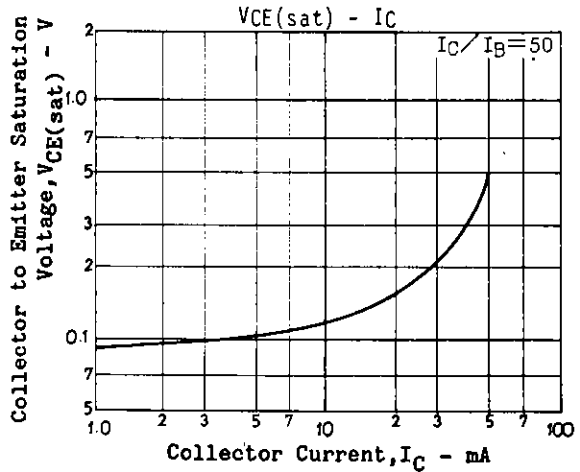
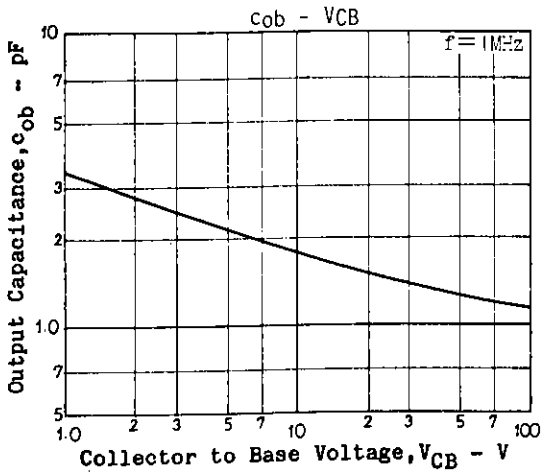
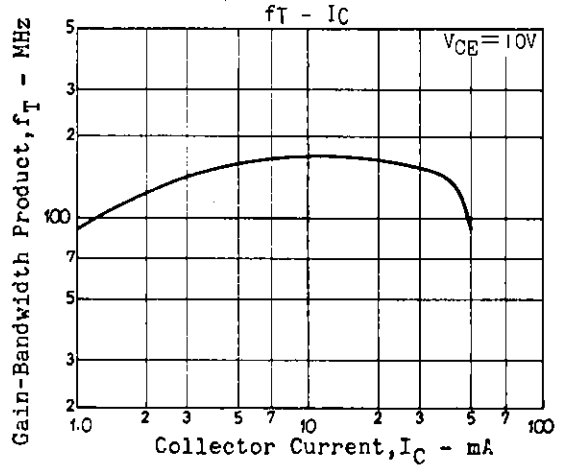
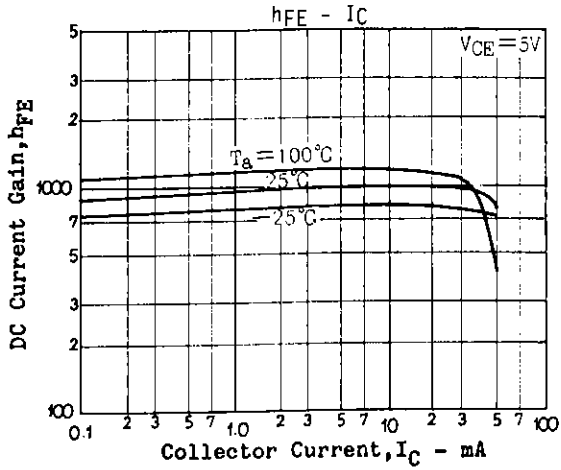
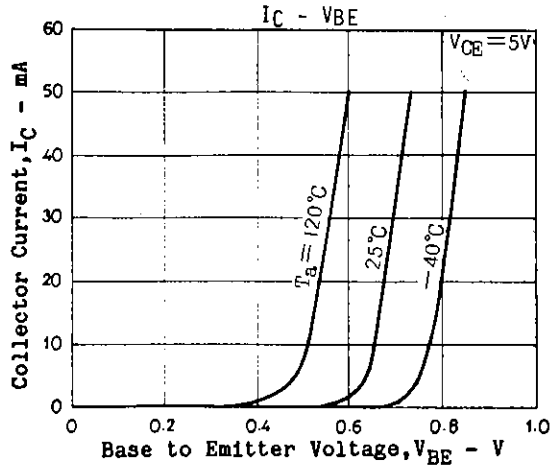
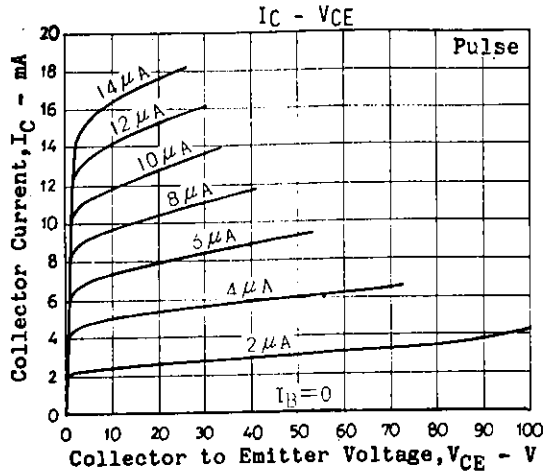
Package Dimensions 2003A
(unit: mm)

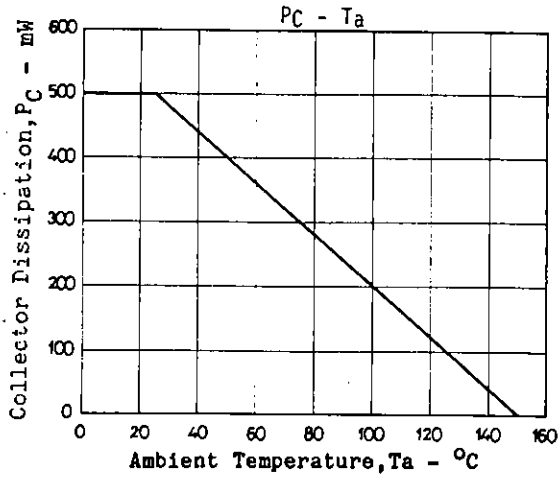


JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter







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